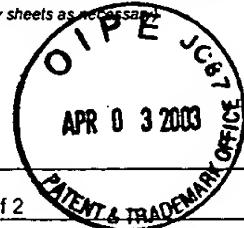


Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
STATEMENT BY APPLICANT**
(Use as many sheets as necessary)



Sheet 1 of 2

Complete if Known	
Application Number	08/902133
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leonard
Group Art Unit	2815
Examiner Name	Eckert II, George

Attorney Docket No: 303.356US1

US PATENT DOCUMENTS

Examiner Initials*	USP Document Number	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	Filing Date If Appropriate
93c	US-4,118,795	10/03/1978	Frye, R. C., et al.	365	222	08/27/1976
m	US-4,384,349	05/17/1983	McElroy, D J.	365	185.02	06/02/1980
9m	US-4,897,710	01/30/1990	Suzuki, A., et al.	357	71	08/18/1997
9m	US-5,317,535	05/31/1994	Talreja, Sanjay S., et al.	365	185	06/19/1992
94c	US-5,366,713	11/22/1994	Sichanugrist, P., et al.	423	346	05/28/1993
94c	US-5,388,069	02/07/1995	Kokubo, Masaya	365	185	03/18/1993
94c	US-5,424,993	06/13/1995	Lee, Roger R., et al.	365	218	11/15/1993
94c	US-5,438,544	08/01/1995	Makino, Takami	365	185	01/28/1994
94c	US-5,441,901	08/15/1995	Candelaria, J.	437	31	06/10/1994
94c	US-5,467,306	11/14/1995	Kaya, Cetin, et al.	365	185.2	10/04/1993
94c	US-5,493,140	02/20/1996	Iguchi, Katsuji	257	316	06/21/1994
94c	US-5,672,889	09/30/1997	Brown,	257	77	
94c	US-5,828,101	10/27/1998	Endo, K.	257	330	03/25/1996
94c	US-5,861,346	01/19/1999	Hamza, A., et al.	438	869	07/27/1995
94c	US-6,031,263	02/29/2000	Forbes, L., et al.	257	315	07/29/1997
94c	US-6,309,907	10/30/2001	Forbes, L., et al.	438	108	08/21/1998

FOREIGN PATENT DOCUMENTS

Examiner Initials*	Foreign Document No	Publication Date	Name of Patentee or Applicant of cited Document	Class	Subclass	T ²

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

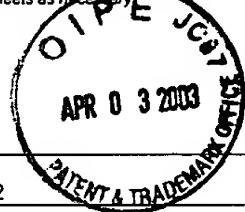
Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
94c		BELTRAM, F., et al., "Memory phenomena in heterojunction structures: Evidence for suppressed thermionic emission", <u>Appl. Phys. Lett.</u> , 53(5), (1988), pp. 376-378	
94c		BOERINGER, DANIEL W., et al., "Avalanche amplification of multiple resonant tunneling through parallel silicon microcrystallites", <u>Physical Rev. B</u> , 51, (1995), pp. 13337-13343	
94c		EDELBERG, E., et al., "Visible Luminescence from Nanocrystalline silicon films produced by plasma enhanced chemical vapor deposition", <u>Appl. Phys. Lett.</u> , 68, (1996), pp. 1415-1417	
94c	/	HYBERTSEN, MARK S., "Absorption and Emission of Light in Nanoscale Silicon Structures", <u>Phys. Rev. Lett.</u> , 72, (1994), pp. 1514-1517	
94c	/	KATO, MASATAKA, et al., "Read-Disturb Degradation Mechanism due to Electron Trapping in the Tunnel Oxide for Low-voltage Flash Memories", <u>IEEE Electron Device Meeting</u> , (1994), pp. 45-48	

EXAMINER

DATE CONSIDERED

8/5/03

Substitute for form 1449A/PTO
**INFORMATION DISCLOSURE
 STATEMENT BY APPLICANT**
 (Use as many sheets as necessary)



Sheet 2 of 2

Complete if Known	
Application Number	08/902133
Filing Date	July 29, 1997
First Named Inventor	Forbes, Leonard
Group Art Unit	2815
Examiner Name	Eckert II, George

Attorney Docket No: 303.356US1

OTHER DOCUMENTS -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
9PC		LOTT, J., et al., "Anisotropic thermionic emission of electrons contained in GaAs/AlAs floating gate device structures", <u>Appl. Phys. Lett.</u> , 55(12), (1989), pp. 1226-1228	
9PC		NEUDECK, P., et al., "Electrical Characterization of a JFET-Accessed GaAs Dynamic RAM Cell", <u>IEEE Electron Device Letters</u> , 10(11), (1989), pp. 477-480	
9PC		QIAN, Q., et al., "Multi-Day Dynamic Storage of Holes at the AlAs/GaAs Interface", <u>IEEE Electron Device Letters</u> , EDL-7(11), (1986), pp. 607-609	
9PC		SCHOENFELD, O., et al., "Formation of Si Quantum dots in Nanocrystalline silicon", <u>Proc. 7th Int. Conf. on Modulated Semiconductor Structures</u> , Madrid, (1995), pp. 605-608	
9PC		TSU, RAPHAEL, et al., "Slow Conductance oscillations in nanoscale silicon clusters of quantum dots", <u>Appl. Phys. Lett.</u> , 65, (1994), pp. 842-844	
9PC		TSU, R., et al., "Tunneling in Nanoscale Silicon Particles Embedded in an a-SiO ₂ Matrix", <u>Abstract, IEEE Device Research Conference</u> , (1996), pp. 178-179	
9PC		YE, QIU-YI, et al., "Resonant Tunneling via Microcrystalline-silicon quantum confinement", <u>Physical Rev. B</u> , 44, (1991), pp. 1806-1811	
9PC		ZHAO, X., et al., "Nanocrystalline Si: a material constructed by Si quantum dots", <u>1st Int. Conf. on Low Dimensional Structures and Devices</u> , Singapore, (1995), pp. 467-471	

EXAMINER

DATE CONSIDERED

8/5/03